

N-Channel 30-V (D-S) Fast Switching MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.0075 at $V_{GS} = 10$ V	17.8
	0.0082 at $V_{GS} = 4.5$ V	17.0

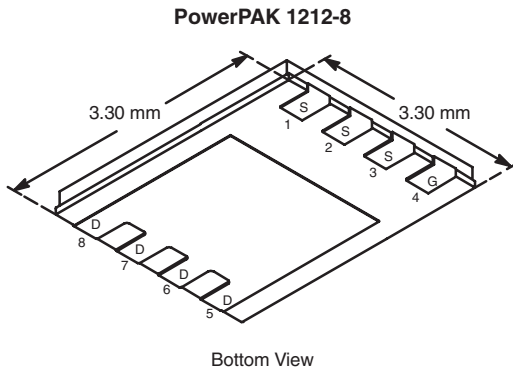
FEATURES

- TrenchFET[®] Power MOSFET
- New Low Thermal Resistance PowerPAK[®] Package with Low 1.07 mm Profile
- 100 % R_g Tested
- Lead (Pb)-free Version is RoHS Compliant



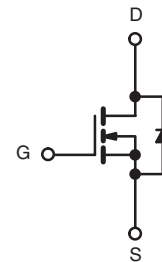
APPLICATIONS

- Synchronous Rectification



Bottom View

Ordering Information: Si7112DN-T1
Si7112DN-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	10 sec	Steady State	Unit
Drain-Source Voltage	V_{DS}	30		V
Gate-Source Voltage	V_{GS}	± 12		
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	17.8	11.3
		$T_A = 70$ °C	14.2	9.1
Pulsed Drain Current	I_{DM}	60		A
Continuous Source Current (Diode Conduction) ^a	I_S	3.2	1.3	
Single Avalanche Current	I_{AS}	L = 0.1 mH	20	
Single Avalanche Energy			E_{AS}	20
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	3.8	1.5
		$T_A = 70$ °C	2.0	0.8
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}		260		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	24	33	°C/W
		Steady State	65	81	
Maximum Junction-to-Case (Drain)	R_{thJC}	1.9	2.4		

Notes:

- Surface Mounted on 1" x 1" FR4 Board.
- See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

MOSFET SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.6		1.5	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	40			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 17.8\text{ A}$		0.006	0.0075	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 17\text{ A}$		0.0065	0.0082	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 17.8\text{ A}$		97		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 3.2\text{ A}, V_{GS} = 0\text{ V}$		0.7	1.2	V
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		260		μF
Output Capacitance	C_{oss}			340		
Reverse Transfer Capacitance	C_{rss}			145		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 17.8\text{ A}$		18	27	nC
Gate-Source Charge	Q_{gs}			6.2		
Gate-Drain Charge	Q_{gd}			3.1		
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.5	1.2	1.8	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \equiv 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		10	15	ns
Rise Time	t_r			10	15	
Turn-Off Delay Time	$t_{d(off)}$			65	100	
Fall Time	t_f			10	15	
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 3.2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		30	60	nC
Body Diode Reverse Recovery Charge	Q_{rr}			18		

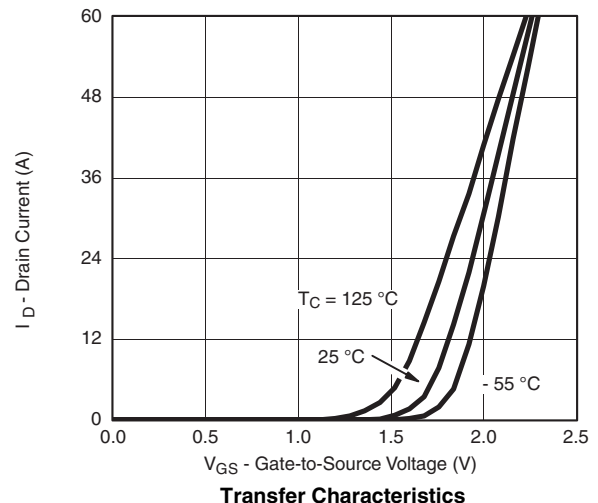
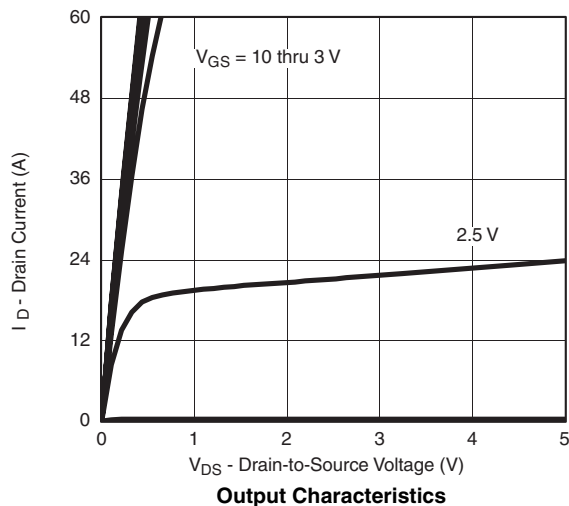
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

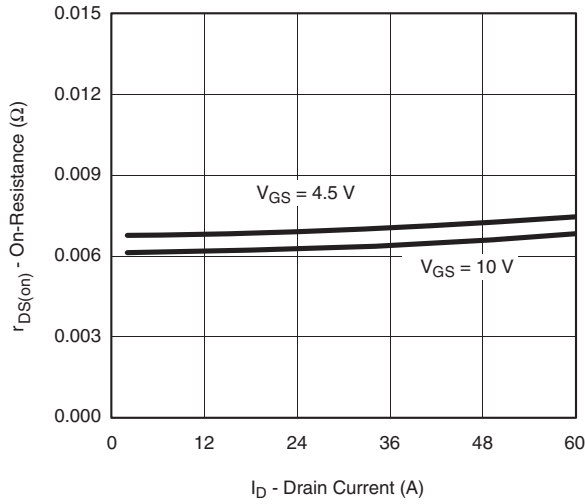
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

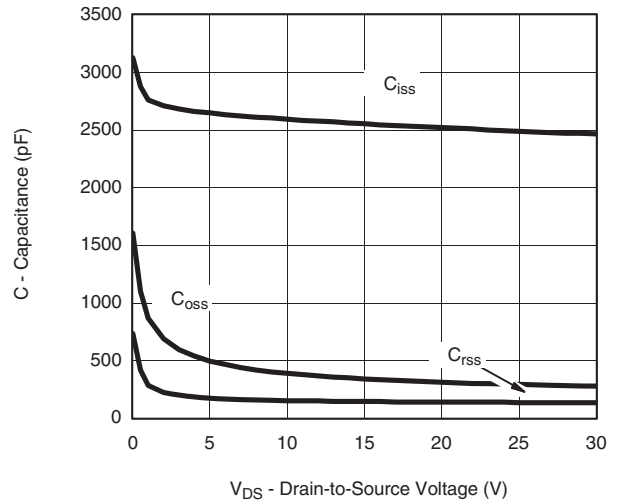
TYPICAL CHARACTERISTICS 25 °C unless noted



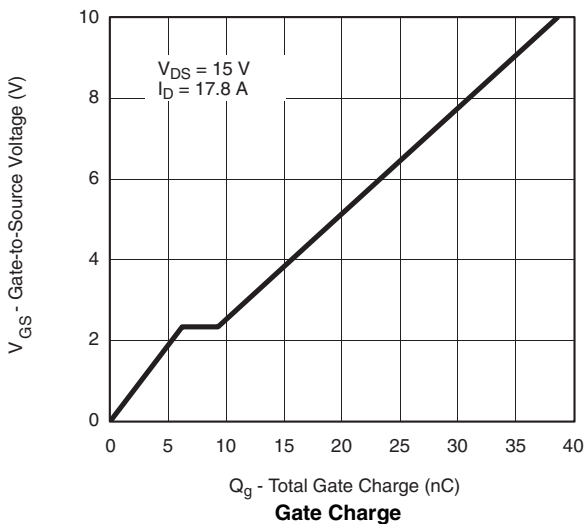
TYPICAL CHARACTERISTICS 25 °C unless noted



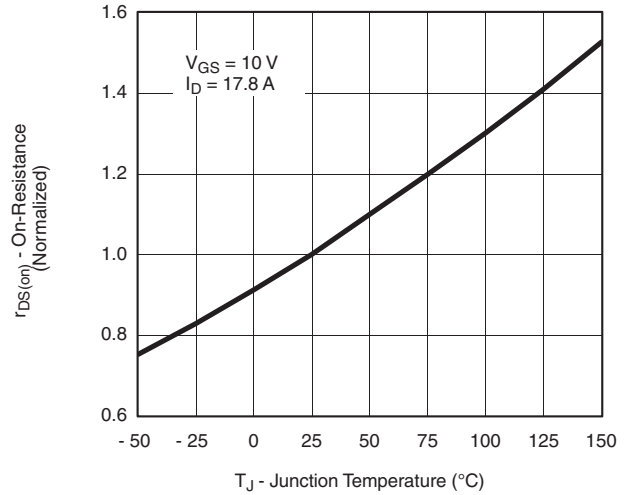
On-Resistance vs. Drain Current



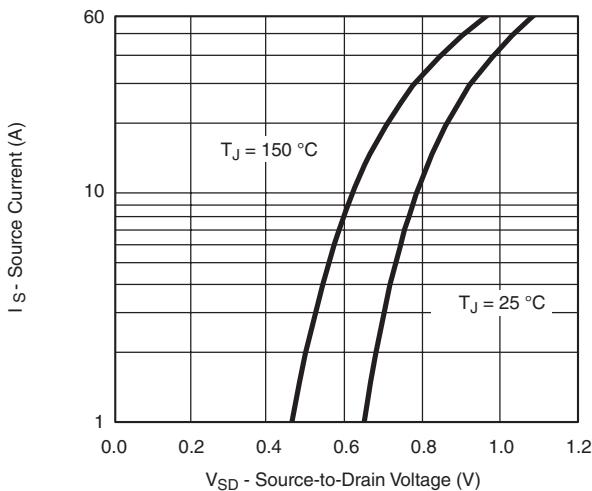
Capacitance



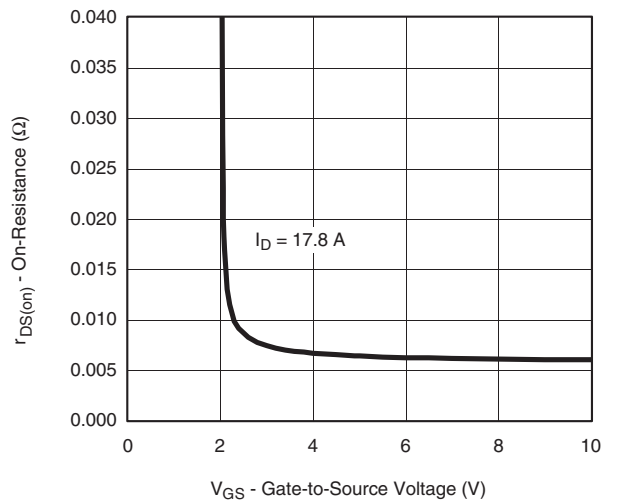
Gate Charge



On-Resistance vs. Junction Temperature

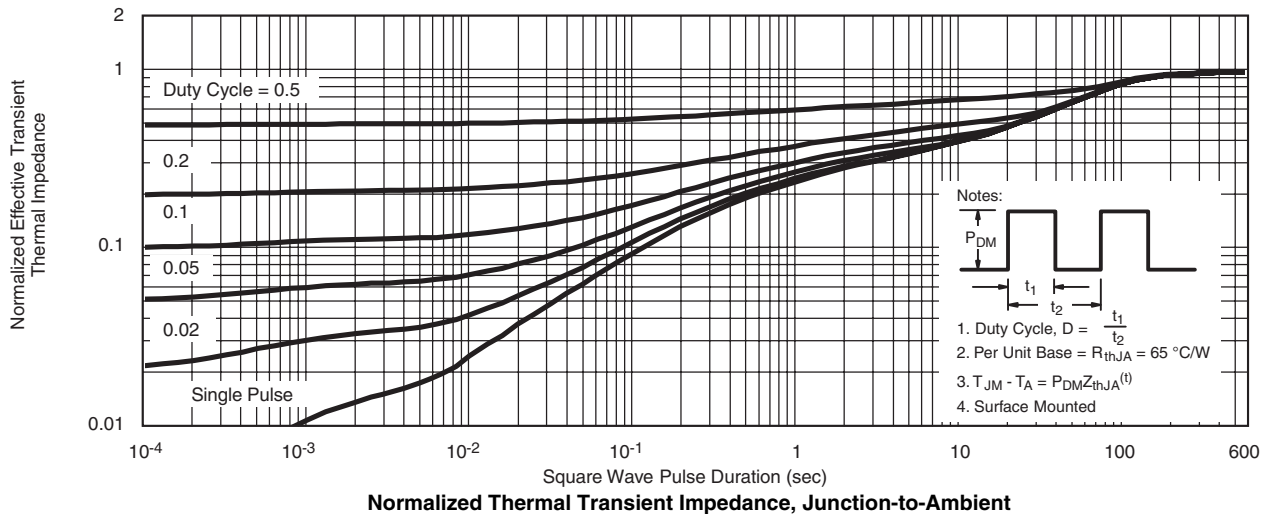
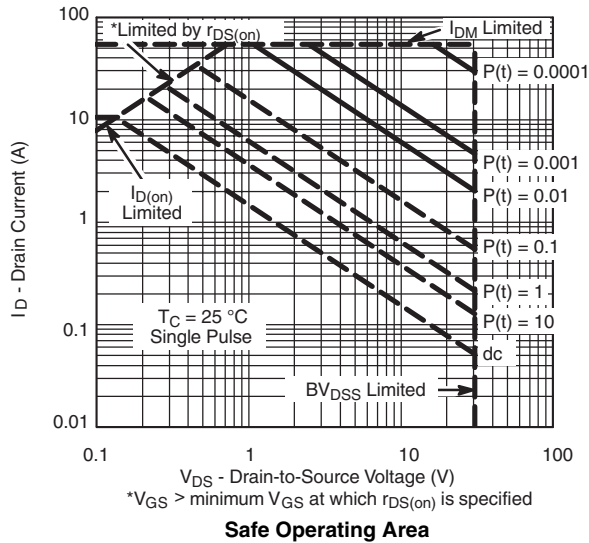
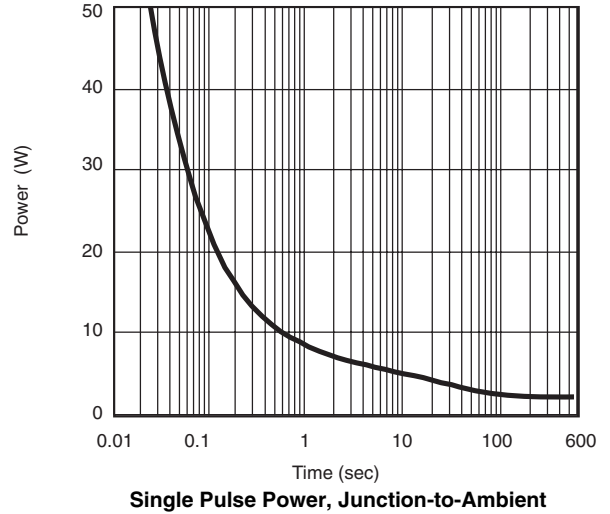
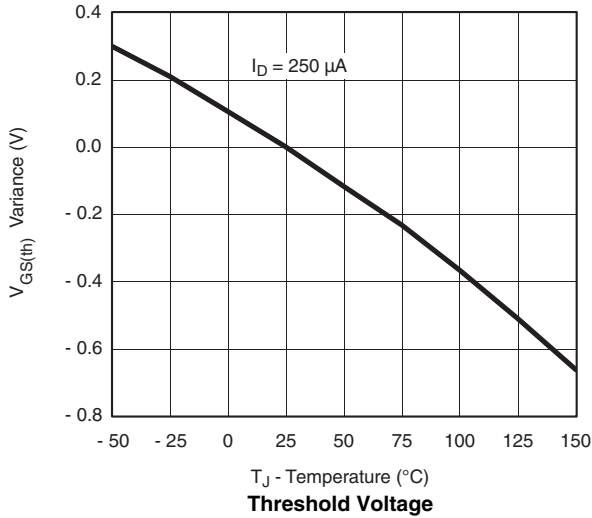


Source-Drain Diode Forward Voltage

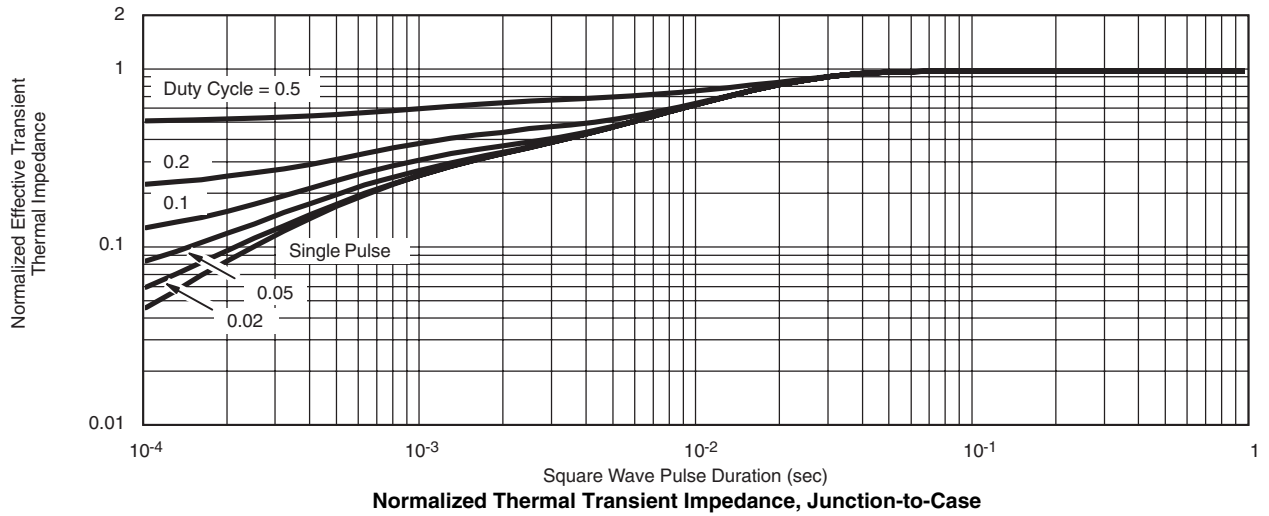


On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C unless noted



TYPICAL CHARACTERISTICS 25 °C unless noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?72864>.



Notice

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.